KTA1664

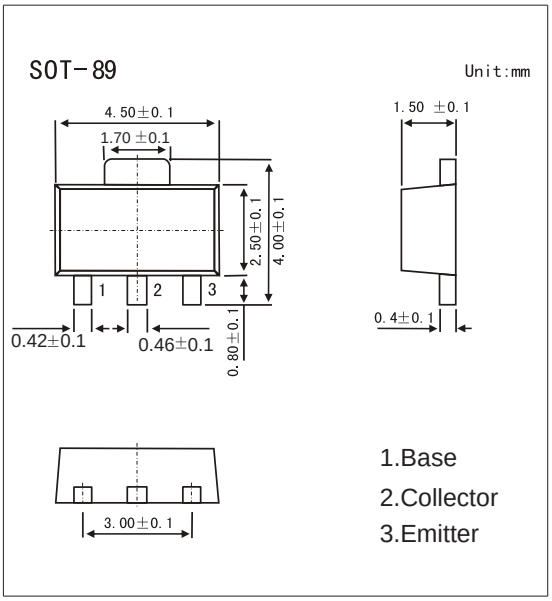
SOT-89 Plastic-Encapsulate Transistors

Features

- 1W (Mounted on Ceramic Substrate)
- Small Flat Package
- Comlementary to KTC4376
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-35	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-800	mA
Base Current	I_B	-160	
Collector Power Dissipation	P_C	500	mW
		1	W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

PACKAGE INFORMATION

Device	Package	Shipping
KTA1664	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -1 mA, I_E=0	-35			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -1 mA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -35V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-20mA			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B=-20mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -1V, I_C= -10mA			-0.8	
DC current gain	h_{FE}	V_{CE}= -1V, I_C= -100mA	100		320	
		V_{CE}= -1V, I_C= -700mA	35			
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		19		pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA		120		MHz

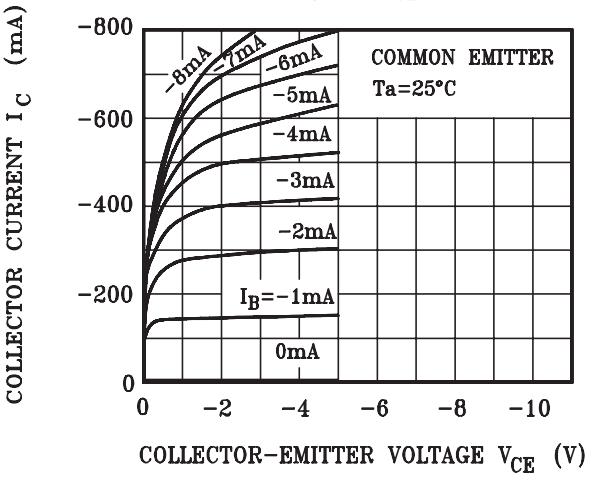
■ Classification of $h_{fe(1)}$

Type	KTA1664-O	KTA1664-Y
Range	100-200	160-320
Marking	RO	RY

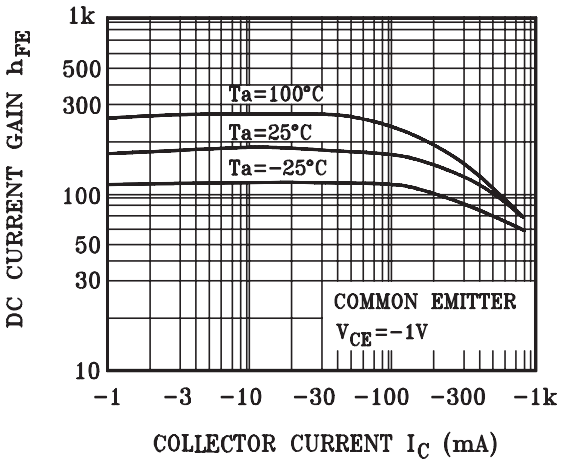
RATINGS AND CHARACTERISTIC CURVES

■ Typical Characterisitics

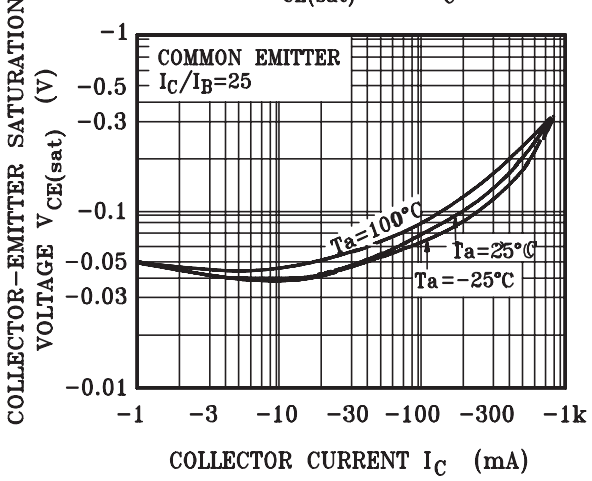
I_C – V_{CE}



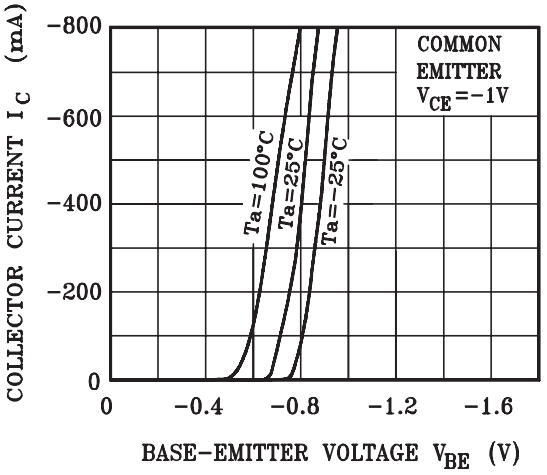
h_{FE} – I_C



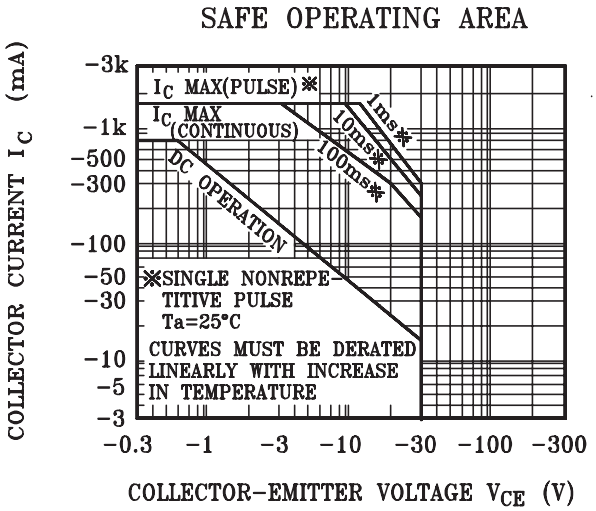
$V_{CE(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta